REMARKS

Claims 22-31 and 41-62 stand rejected. Claims 22, 24, 25, 28, 29, and 31 have been amended; claims 43, 46, 48 and 49-62 have been cancelled; and claims 22-31, 41-42, 44-45 and 47 are pending.

Claims 22-31 and 41-62 stand rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such as way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Applicant requests reconsideration of this rejection.

Claim 22 has been amended and as amended recites a semiconductor processing method that includes forming an antireflective material layer comprising silicon, oxygen and nitrogen over a substrate. Claim 22 further recites, after forming the antireflective material layer, annealing at least a portion of the antireflective material layer at a temperature of greater than 400°C. Applicant believes amended claim 22 satisfies the requirements of the first paragraph of 35 U.S.C. §112, for at least the reason that "greater than 400°C" is literally described on page 6 of the application.

For a reference to anticipate a claim, the reference must teach every element of the claim (MPEP §2131, 8th Ed.). Furthermore, to establish a prima facie case of obviousness, the prior art reference (or references when combined) must teach or suggest all the claim limitations (MPEP §706.02(j)).

Claim 22 is allowable for at least the reason that it recites, after forming an antireflective material comprising silicon, oxygen and nitrogen, annealing the antireflective material layer at a temperature of greater than 400°C. The prior art of record neither

teaches or suggests the annealing of an antireflective material comprising silicon, oxygen and nitrogen at a temperature greater than 400°C.

Claims 23, 41, and 42 depend from claim 22 and are allowable for at least the reasons discussed above regarding claim 22.

Claim 24 has been amended and as amended recites a semiconductor processing method that includes forming an antireflective material layer comprising silicon, oxygen and nitrogen over a substrate. Claim 24 further recites, after forming the antireflective material layer, annealing the antireflective material layer at a temperature of greater than 400°C. As discussed above, the prior art of record neither teaches nor suggests annealing an antireflective material comprising silicon, oxygen and nitrogen at a temperature of greater than 400°C. For at least the reason that the prior art neither teaches or suggests all of the limitations of claim 24, claim 24 is allowable.

Claims 25-27, 44, and 45 depend from claim 24 and are allowable for at least the reasons discussed above regarding claim 24.

Claim 28 has been amended and as amended recites a semiconductor processing method that includes forming a solid antireflective material layer comprising silicon, oxygen and nitrogen over a substrate. Claim 28 further recites, after forming the solid antireflective material layer, altering optical properties of the solid antireflective material layer by annealing the antireflective material layer at a temperature greater than 400°C. As stated above 28 is allowable for at least the reason that claim 28 recites a limitation that is not taught or suggested by the prior art of record. Applicant requests allowance of claim 28 in the Examiner's next action.

Claims 29-31 and 47 depend from claim 28 and are allowable for at least the reasons discussed above regarding claim 28.

A supplemental information disclosure statement is submitted herewith.

Claims 22, 24, 25, 28, 29, and 31 have been amended; claims 43, 46, and 48-62 have been cancelled; and a supplemental information disclosure statement has been submitted. Claims 22-31, 41-42, 44-45, and 47 remain pending in the application. Applicant requests allowance of the pending claims in the Examiner's next action.

Respectfully submitted,

Dated: 7/3/03 By: _____

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